

## **TSM2314**

### 20V N-Channel MOSFET



**SOT-23** 

#### Pin Definition:

- 1. Gate
- 2. Source

#### 3. Drain

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
20	33 @ V <sub>GS</sub> = 4.5V	4.9
	40 @ V <sub>GS</sub> = 2.5V	4.4
	51 @ V <sub>GS</sub> = 1.8V	3.9

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

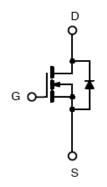
#### **Application**

- Load Switch
- PA Switch

### **Ordering Information**

Part No.	Package	Packing
TSM2314CX RF	SOT-23	T&R

### **Block Diagram**



N-Channel MOSFET

### Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	20V	V	
Gate-Source Voltage		$V_{GS}$	±12	V	
Continuous Drain Current, V <sub>GS</sub> @4.5V	•	I <sub>D</sub>	4.9	Α	
Pulsed Drain Current, V <sub>GS</sub> @4.5V	d Drain Current, V <sub>GS</sub> @4.5V		15	А	
Continuous Source Current (Diode Co	nduction) <sup>a,b</sup>	I <sub>S</sub>	1.0	А	
Mayimum Dayar Dissination	Ta = 25 °C		1.25	<b>10</b> /	
Maximum Power Dissipation	Ta = 75 °C	P <sub>D</sub>	0.8	W	
Operating Junction Temperature		T <sub>J</sub>	+150	°C	
Operating Junction and Storage Temp	erature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖JF	40	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO <sub>JA</sub>	75	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.



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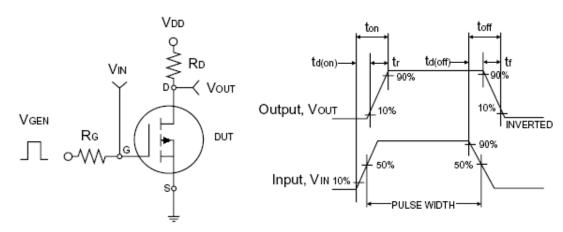


## **Electrical Specifications**

Parameter	Conditions	Symbol	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	20			V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	0.45			V	
Gate Body Leakage	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	I <sub>GSS</sub>			±1.5	μΑ	
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	μΑ	
On-State Drain Current	$V_{DS} \ge 10V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	15			Α	
	$V_{GS} = 4.5V, I_D = 4.9A$			27	33		
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 4.4A$	R <sub>DS(ON)</sub>		33	40	mΩ	
	$V_{GS} = 1.8V, I_D = 3.9A$			42	51		
Forward Transconductance	$V_{DS} = 15V, I_D = 5.0A$	9 <sub>fs</sub>		40		S	
Diode Forward Voltage	I <sub>S</sub> = 1.0A, V <sub>GS</sub> = 0V	$V_{SD}$		0.8	1.2	V	
Dynamic <sup>b</sup>	• • • • • • • • • • • • • • • • • • • •						
Total Gate Charge	- \/ - 40\/   - 5 0A	$Q_g$		11	14		
Gate-Source Charge	$V_{DS} = 10V, I_D = 5.0A,$ $V_{GS} = 4.5V$	$Q_{gs}$		1.5		nC	
Gate-Drain Charge	V <sub>GS</sub> - 4.5 V	$Q_{gd}$		2.1			
Input Capacitance		C <sub>iss</sub>		900			
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	C <sub>oss</sub>		140		pF	
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		100			
Switching <sup>c</sup>							
Turn-On Delay Time	$V_{DD} = 10V, R_L = 10\Omega,$	t <sub>d(on)</sub>		0.53	8.0		
Turn-On Rise Time		t <sub>r</sub>		1.4	2.2	nC	
Turn-Off Delay Time	$I_D = 1A$ , $V_{GEN} = 4.5V$ ,	t <sub>d(off)</sub>		13.5	20	nS	
Turn-Off Fall Time	$R_G = 6\Omega$	t <sub>f</sub>		5.9	9		

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

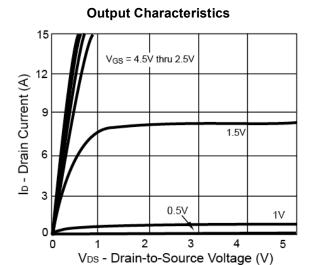




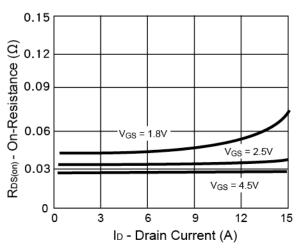




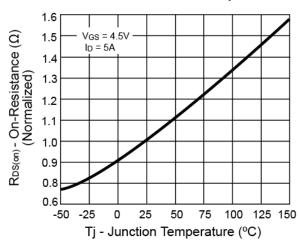
#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)



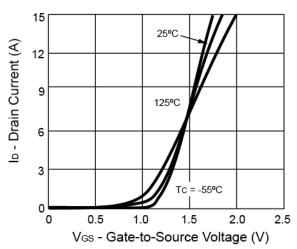
#### On-Resistance vs. Drain Current



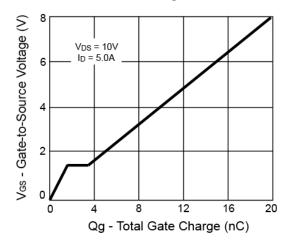
#### On-Resistance vs. Junction Temperature



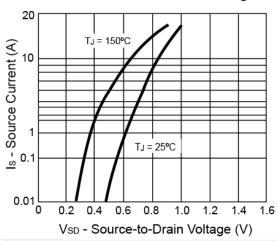
#### **Transfer Characteristics**



#### **Gate Charge**



#### Source-Drain Diode Forward Voltage





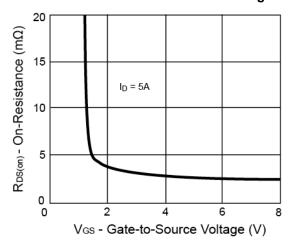


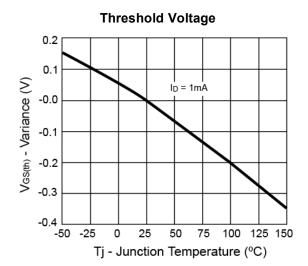




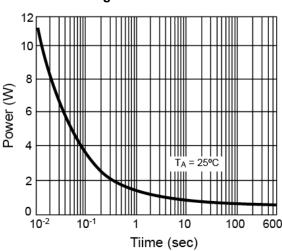
#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

#### On-Resistance vs. Gate-Source Voltage

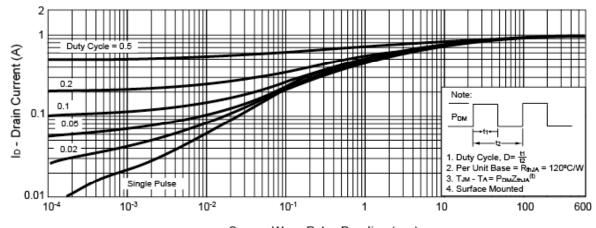




#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



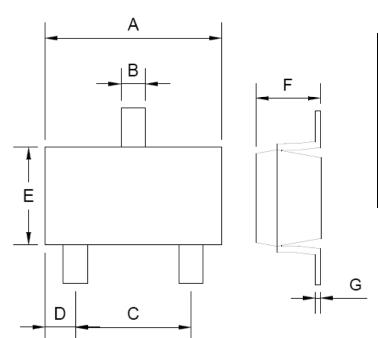
Square Wave Pulse Duration (sec)

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## **SOT-23 Mechanical Drawing**



SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	2.88	2.91	0.113	0.115	
В	0.39	0.42	0.015	0.017	
С	1.78	2.03	0.070	0.080	
D	0.51	0.61	0.020	0.024	
Е	1.59	1.66	0.063	0.065	
F	1.04	1.08	0.041	0.043	
G	0.07	0.09	0.003	0.004	



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